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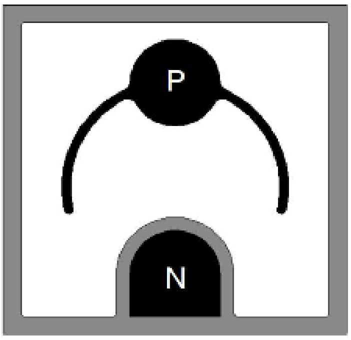
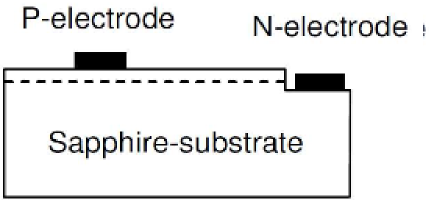
ELC-525-34

Radiation	Type	Electrodes
green	GaN / sapphire	N+P-up





Chip size: 15 mil x 15 mil (380 ± 25 µm x 380 ± 25 µm)

Thickness: 3.5 mil (90 ± 10 µm)

N, P bonding pads: 4 mil (100 ± 10 µm), Au alloy

Absolute Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Symbol	Rating	Unit
Forward current	I_F	30	mA

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Symbol	Cond.	Min	Typ	Max	Unit
Forward voltage	V_F	I_F=20 mA	2.8	3.0	3.8	V
Reverse current	I_R	V_R=5 V			2	µA
Luminous intensity*	I_V	I_F=20 mA		850	1200	mcd
Radiant power**	Φ_e	I_F=20 mA		9		mW
TK of radiant power	$TK\Phi_e$	I_F=20 mA		-0.12		%/K
Dominant wavelength	λ_D	I_F=20 mA	515	525	535	nm
FWHM	$\Delta\lambda_{0.5}$	I_F=20 mA		35		nm

*Measured on gold plate; **measured on TO-header with epoxy encapsulation

Packing

Dice on adhesive film with wire-bond on top

RoHS COMPLIANT CE